Elektronische Bauelemente

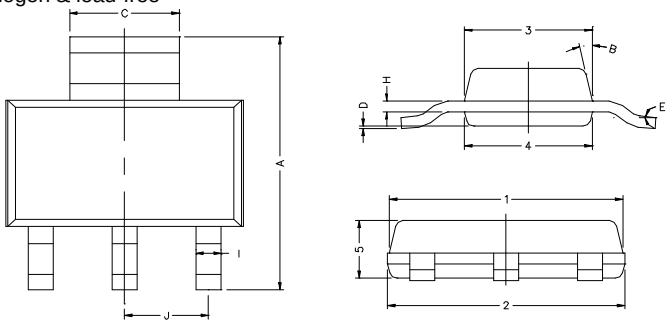
PZT157

PNP Transistor

Silicon Planar High Performance Transistor

RoHS Compliant Product
A suffix of ñ-Cò specifies halogen & lead-free

SOT-223

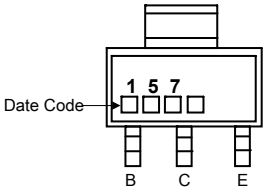


Description

The PZT157 is designed for general purpose switching and amplifier applications.

Features

* 3 Amps Continous Current
* -60 Volt V_{CEO}
* Low Saturation Voltages



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	6.70	7.30	B	13°TYP.	
C	2.90	3.10	J	2.30 REF.	
D	0.02	0.10	1	6.30	6.70
E	0°	10°	2	6.30	6.70
I	0.60	0.80	3	3.30	3.70
H	0.25	0.35	4	3.30	3.70
			5	1.40	1.80

MAXIMUM RATINGS* (T_{amb}=25°C, unless otherwise specified)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	-80	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current (DC)	-3	A
	Collector Current (Pulse)	-6	
P_D	Total Power Dissipation	2	W
T_J,T_{stg}	Junction and Storage Temperature	-55~+150	°C

ELECTRICAL CHARACTERISTICS Tamb=25°C unless otherwise specified

Parameter	Symbol	Min	Typ.	Max	Unit	Test Conditions
Collector-Base Breakdown Voltage	BV_{CBO}	-80	-	-	V	I_C=-100μA, I_E=0
Collector-Emitter Breakdown Voltage	*BV_{CEO}	-60	-	-	V	I_C=-10mA, I_B=0
Emitter-Base Breakdown Voltage	BV_{EBO}	-5	-	-	V	I_E=-100μA, I_C=0
Collector-Base Cutoff Current	I_{CBO}	-	-	-100	nA	V_{CB}=-60V, I_E=0
Emitter-Base Cutoff Current	I_{EBO}	-	-	-100	nA	V_{EB}=-4V,I_C=0
Collector Saturation Voltage	*V_{CE}(sat)1	-	-150	-300	mV	I_C=-1A,I_B=-100mA
	*V_{CE}(sat)2	-	-450	-600		I_C=-3A,I_B=-300mA
Base Saturation Voltage	*V_{BE}(sat)	-	-0.9	-1.25	V	I_C=-1A,I_B=-100mA
Base-Emitter Voltage	*V_{BE}(on)	-	-0.8	-1.0	V	I_C=-1A,V_{CE}=-2V
DC Current Gain	*h_{FE}1	70	200	-		V_{CE}=-2V, I_C=-50mA
	*h_{FE}2	100	200	300		V_{CE}=-2V, I_C=-500mA
	*h_{FE}3	80	170	-		V_{CE}=-2V, I_C=-1A
	*h_{FE}4	40	150	-		V_{CE}=-2V, I_C=-2A
Gain-Bandwidth Product	fT	100	140	-	MHz	V_{CE}=-5V, I_C=-100mA, f=100MHz
Output Capacitance	C_{ob}	-	-	30	pF	V_{CB}=-10V, f=1MHz
On-Time	T_{on}	-	40	-	nS	V_{CC}=-10V,I_C=-500mA,I_{B1}=I_{B2}=-50mA
Off-Time	T_{off}	-	450	-		

*Measured under pulse condition. Pulse width≦300μs, Duty Cycle≦2%
Spice parameter data is available upon request for this device.

Characteristics Curve